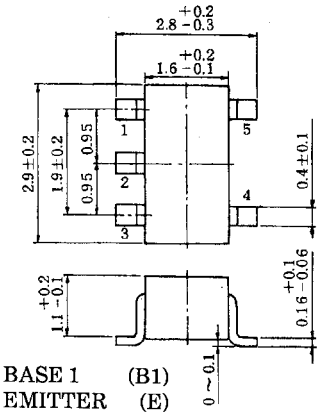
TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

RN2507,RN2508,RN2509

Switching, Inverter Circuit, Interface Circuit
And Driver Circuit Applications

Unit in mm

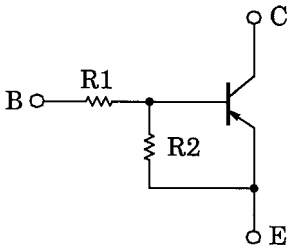


JEDEC	—
EIAJ	—
TOSHIBA	2-3L1A

Weight: 0.014g

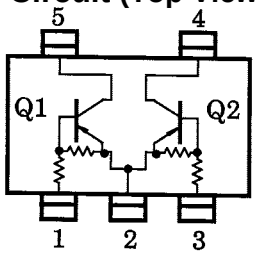
- Including two devices in SMV (super mini type with 5 leads)
- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- Complementary to RN1507~RN1509

Equivalent Circuit and Bias Resistor Values



Type No.	R1 (kΩ)	R2 (kΩ)
RN2507	10	47
RN2508	22	47
RN2509	47	22

Equivalent Circuit (Top View)



Maximum Ratings (Ta = 25°C) (Q1, Q2 Common)

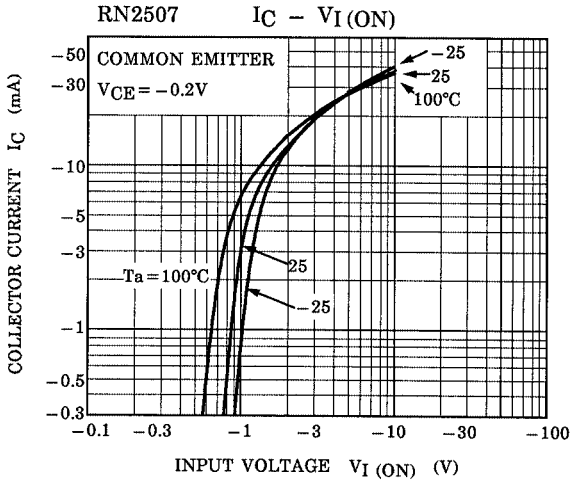
Characteristic		Symbol	Rating	Unit
Collector-base voltage	RN2507~RN2509	V_{CBO}	−50	V
Collector-emitter voltage		V_{CEO}	−50	V
Emitter-base voltage	RN2507	V_{EBO}	−6	V
	RN2508		−7	
	RN2509		−15	
Collector current	RN2507~RN2509	I_C	−100	mA
Collector power dissipation		P_C*	300	mW
Junction temperature		T_j	150	°C
Storage temperature range		T_{stg}	−55~150	°C

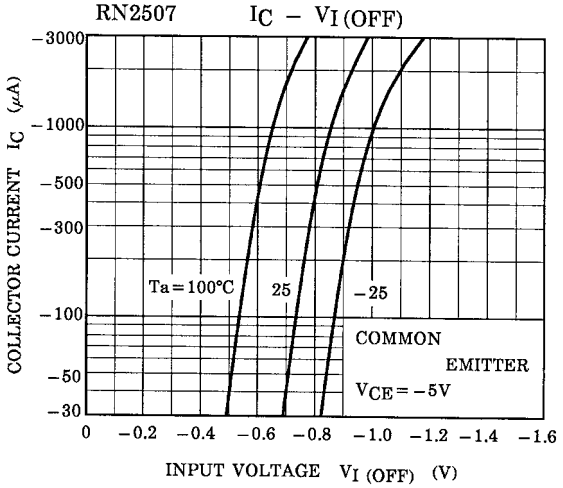
* Total rating

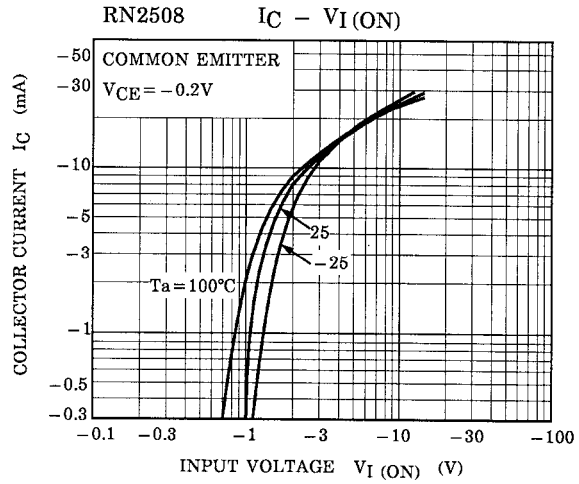
Electrical Characteristics (Ta = 25°C) (Q1, Q2 Common)

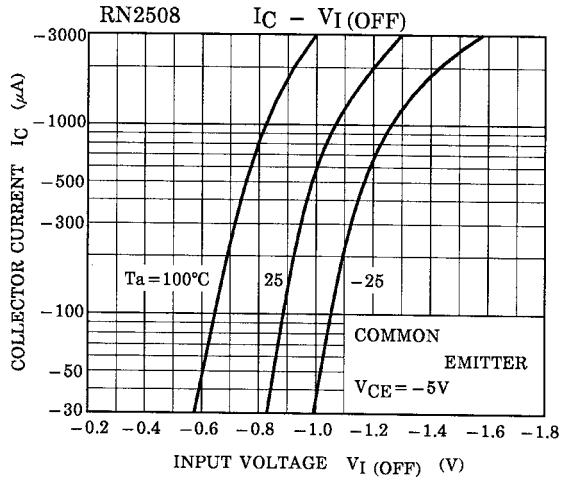
Characteristic		Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	RN2507~RN2509	I_{CBO}	—	V_{CB} = −50V, I_E = 0	—	—	−100	nA
		I_{CEO}	—	V_{CE} = −50V, I_B = 0	—	—	−500	nA
Emitter cut-off current	RN2507	I_{EBO}	—	V_{EB} = −6V, I_C = 0	−0.081	—	−0.15	mA
	RN2508		—	V_{EB} = −7V, I_C = 0	−0.078	—	−0.145	
	RN2509		—	V_{EB} = −15V, I_C = 0	−0.167	—	−0.311	
DC current gain	RN2507	h_{FE}	—	V_{CE} = −5V, I_C = −10mA	80	—	—	—
	RN2508		—		80	—	—	
	RN2509		—		70	—	—	
Collector-emitter saturation voltage	RN2507~RN2509	$V_{CE\ (sat)}$	—	I_C = −5mA, I_B = −0.25mA	—	−0.1	−0.3	V
Input voltage (ON)	RN2507	$V_{I\ (ON)}$	—	V_{CE} = −0.2V, I_C = −5mA	−0.7	—	−1.8	V
	RN2508		—		−1.0	—	−2.6	
	RN2509		—		−2.2	—	−5.8	
Input voltage (OFF)	RN2507	$V_{I\ (OFF)}$	—	V_{CE} = −5V, I_C = −0.1mA	−0.5	—	−1.0	V
	RN2508		—		−0.6	—	−1.16	
	RN2509		—		−1.5	—	−2.6	
Translation frequency	RN2507~RN2509	f_T	—	V_{CE} = −10V, I_C = −5mA	—	200	—	MHz
Collector output capacitance	RN2507~RN2509	C_{ob}	—	V_{CB} = −10V, I_E = 0 f = 1MHz	—	3	6	pF
Input resistor	RN2507	R1	—	—	7	10	13	kΩ
	RN2508		—		15.4	22	28.6	
	RN2509		—		32.9	47	61.1	
Resistor ratio	RN2507	R1/R2	—	—	0.191	0.213	0.232	—
	RN2508		—		0.421	0.468	0.515	
	RN2509		—		1.92	2.14	2.35	

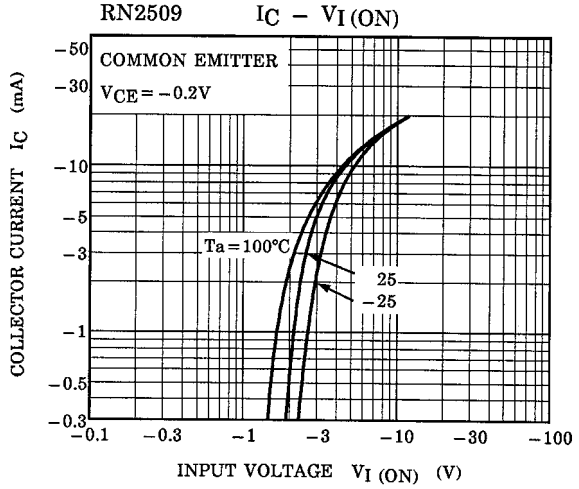
(Q1, Q2 Common)

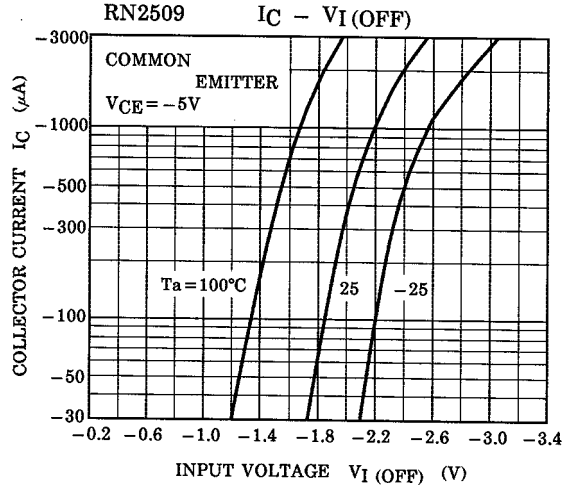

RN2507 I_C – $V_{I\,(ON)}$
COMMON EMITTER
V_{CE} = −0.2V
Ta = 100°C
25
−25
COLLECTOR CURRENT I_C (mA)
INPUT VOLTAGE $V_{I\,(ON)}$ (V)


RN2507 I_C – $V_{I\,(OFF)}$
Ta = 100°C
25
−25
COMMON EMITTER
V_{CE} = −5V
COLLECTOR CURRENT I_C (μA)
INPUT VOLTAGE $V_{I\,(OFF)}$ (V)

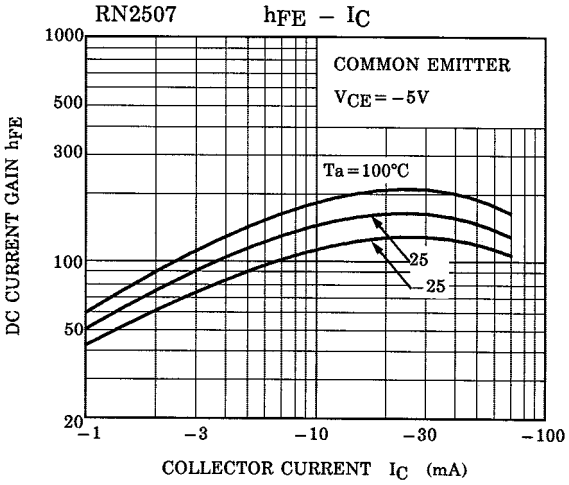

RN2508 I_C – $V_{I\,(ON)}$
COMMON EMITTER
V_{CE} = −0.2V
Ta = 100°C
25
−25
COLLECTOR CURRENT I_C (mA)
INPUT VOLTAGE $V_{I\,(ON)}$ (V)

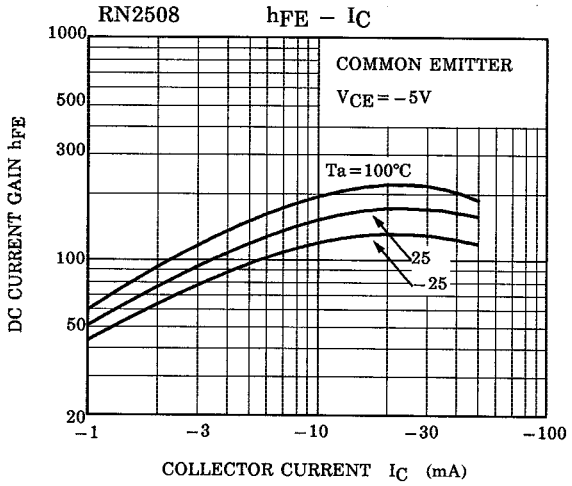

RN2508 I_C – $V_{I\,(OFF)}$
Ta = 100°C
25
−25
COMMON EMITTER
V_{CE} = −5V
COLLECTOR CURRENT I_C (μA)
INPUT VOLTAGE $V_{I\,(OFF)}$ (V)

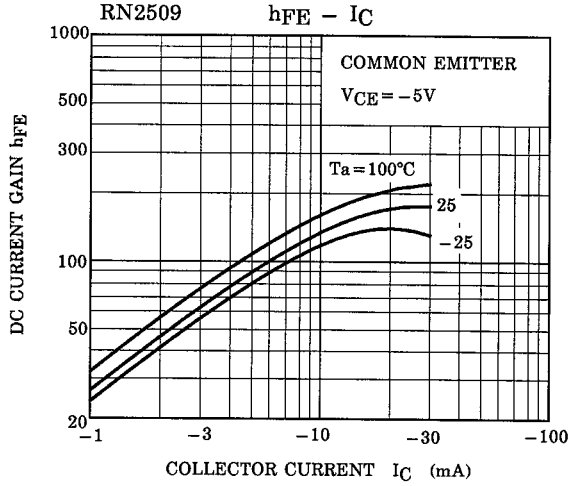

RN2509 I_C – $V_{I\,(ON)}$
COMMON EMITTER
V_{CE} = −0.2V
Ta = 100°C
25
−25
COLLECTOR CURRENT I_C (mA)
INPUT VOLTAGE $V_{I\,(ON)}$ (V)

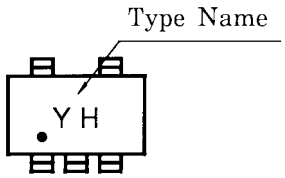
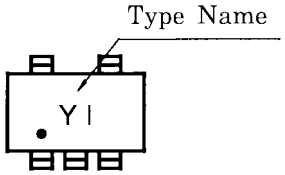
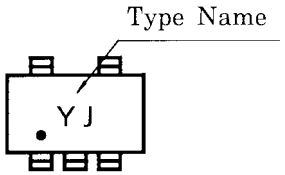

RN2509 I_C – $V_{I\,(OFF)}$
COMMON EMITTER
V_{CE} = −5V
Ta = 100°C
25
−25
COLLECTOR CURRENT I_C (μA)
INPUT VOLTAGE $V_{I\,(OFF)}$ (V)

(Q1, Q2 Common)


RN2507 hFE – IC
COMMON EMITTER
VCE = –5V
Ta = 100°C
25
–25
DC CURRENT GAIN hFE
COLLECTOR CURRENT IC (mA)
1000
500
300
100
50
20
–1
–3
–10
–30
–100


RN2508 hFE – IC
COMMON EMITTER
VCE = –5V
Ta = 100°C
25
–25
DC CURRENT GAIN hFE
COLLECTOR CURRENT IC (mA)
1000
500
300
100
50
20
–1
–3
–10
–30
–100


RN2509 hFE – IC
COMMON EMITTER
VCE = –5V
Ta = 100°C
25
–25
DC CURRENT GAIN hFE
COLLECTOR CURRENT IC (mA)
1000
500
300
100
50
20
–1
–3
–10
–30
–100

Type Name	Marking
RN2507	
RN2508	
RN2509	

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